

ABSTRACT

SPUTTERING TARGET

A sputtering target that can be used for forming a buffer layer that enables magnetic crystal grains in a magnetic recording layer granular film to be well separated each other when the magnetic
5 recording layer granular film is stacked above a Ru underlayer is provided.

The sputtering target contains a metal and an oxide, wherein:
the contained metal becomes a nonmagnetic metal including an hcp
10 structure if the entirety of the contained metal is made into a single metal, the lattice constant "a" of the hcp structure included in the nonmagnetic metal being 2.59 Å or more and 2.72 Å or less;
the contained metal includes 4at% or more of metallic Ru relative to the whole amount of the contained metal; and the sputtering target
15 contains 20 vol% or more and 50 vol% or less of the oxide relative to the entire sputtering target, the melting point of the contained oxide being 1700°C or more.